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May 2014



FDA28N50

N-Channel UniFETTM MOSFET 500 V, 28 A, 155 m Ω

Features

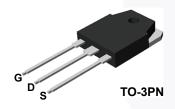
- $R_{DS(on)}$ = 122 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 14 A
- Low Gate Charge (Typ. 80 nC)
- Low C_{rss} (Typ. 42 pF)
- · 100% Avalanche Tested
- · RoHS Compliant

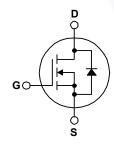
Applications

- PDP TV
- · Uninterruptible Power Supply
- · AC-DC Power Supply

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter			FDA28N50	Unit
V_{DSS}	Drain to Source Voltage			500	V
V _{GSS}	Gate to Source Voltage			±30	V
ı	Drain Current	- Continuous (T _C = 25°C)		28	А
ID	Dialii Cuitelli	- Continuous (T _C = 100°C)		17	A
I _{DM}	Drain Current	- Pulsed	(Note 1)	112	Α
E _{AS}	Single Pulsed Avalanche Energy (Note 2)			2391	mJ
I _{AR}	Avalanche Current		(Note 1)	28	Α
E _{AR}	Repetitive Avalanche Energy		(Note 1)	31	mJ
dv/dt	Peak Diode Recovery dv/	dt	(Note 3)	5	V/ns
D	Dower Dissipation	(T _C = 25°C)		310	W
P_{D}	Power Dissipation	- Derate Above 25°C		2.5	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range			-55 to +150	οС
T _L	Maximum Lead Temperat	ture for Soldering, 1/8" from Case for	5 Seconds	300	°C

Thermal Characteristics

Symbol	Parameter	FDA28N50	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.4	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max. 40		5/88

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDA28N50	FDA28N50	TO-3PN	Tube	N/A	N/A	30 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V, T_J = 25^{\circ} C$	500	-	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	-	0.59	-	V/°C
1	I _{DSS} Zero Gate Voltage Drain Current	V _{DS} = 500 V, V _{GS} = 0 V	-	-	1	μА
I _{DSS} Zero (Zero Gate Voltage Drain Current	$V_{DS} = 400 \text{ V}, T_{C} = 125^{\circ}\text{C}$	-	-	10	μΑ
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	±100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	3.0	-	5.0	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 14 A	1	0.122	0.155	Ω
g _{FS}	Forward Transconductance	V _{DS} = 20 V, I _D = 14 A	-	34	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 05 V V 0 V		-	3866	5140	pF
C _{oss}	Output Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1 MHz	Ī	-	576	766	pF
C _{rss}	Reverse Transfer Capacitance	1 = 1 WH12	Ī	-\	42	63	pF
Q _{g(tot)}	Total Gate Charge at 10V	V _{DS} = 400 V, I _D = 28 A,		-	80	105	nC
Q _{gs}	Gate to Source Gate Charge	V _{GS} = 10 V	Ī	-	21	-	nC
Q_{gd}	Gate to Drain "Miller" Charge	(No	te 4)	-	32	-	nC

Switching Characteristics

t _{d(on)}	Turn-On Delay Time			-	56	122	ns
t _r	Turn-On Rise Time	$V_{DD} = 250 \text{ V}, I_D = 28 \text{ A},$		-	126	262	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} = 10 V, R_G = 25 Ω		-	210	430	ns
t _f	Turn-Off Fall Time		(Note 4)	-	110	230	ns

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	28	Α
I _{SM}	Maximum Pulsed Drain to Source Diode F	orward Current	-	-	112	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 28 A	-	-	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 28 A,	-	530	-	ns
Q _{rr}	Reverse Recovery Charge	dI _F /dt = 100 A/μs	-	8	/ -	μС

Notes:

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. L = 6.1 mH, I_{AS} = 28 A, V_{DD} = 50 V, R_G = 25 Ω , starting T_J = 25°C.
- 3. I_{SD} \leq 28 A, di/dt \leq 200 A/µs, V_{DD} \leq BV_DSS, starting T_J = 25°C.
- Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

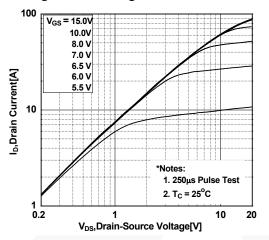


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

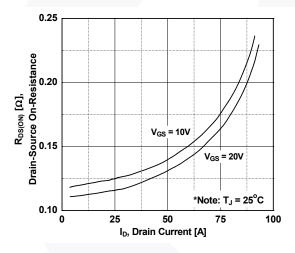


Figure 5. Capacitance Characteristics

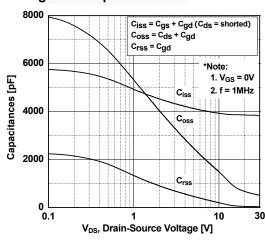


Figure 2. Transfer Characteristics

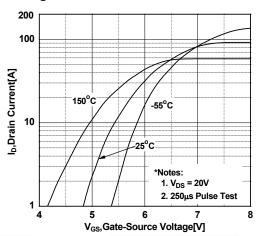


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

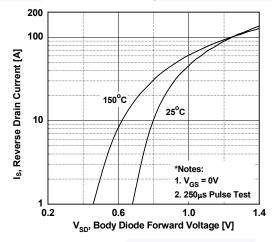
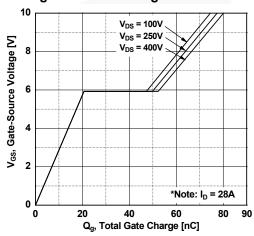


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

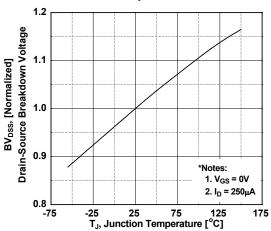


Figure 8. On-Resistance Variation vs. Temperature

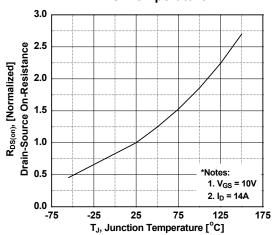


Figure 9. Maximum Safe Operating Area

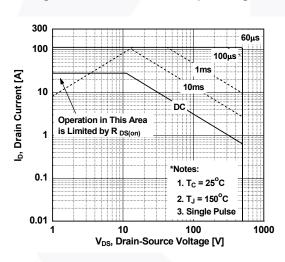


Figure 10. Maximum Drain Current vs. Case Temperature

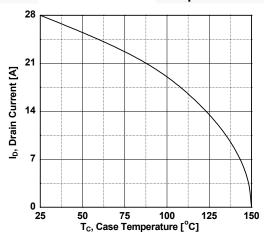
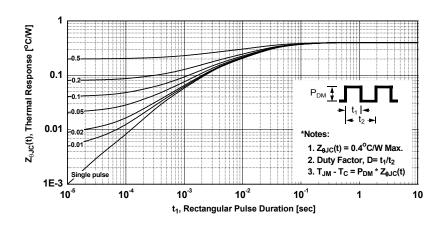


Figure 11. Transient Thermal Response Curve



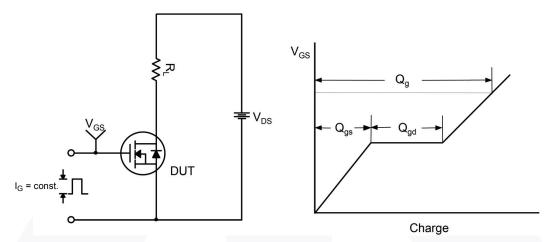


Figure 12. Gate Charge Test Circuit & Waveform

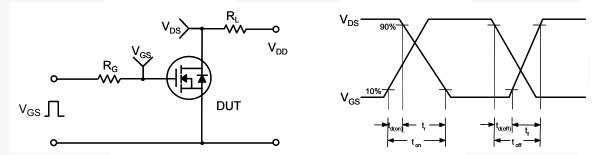


Figure 13. Resistive Switching Test Circuit & Waveforms

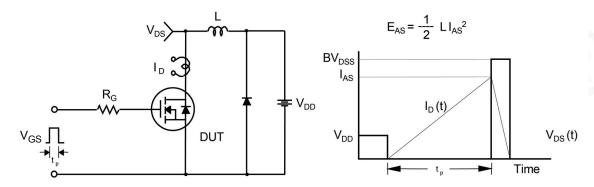


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

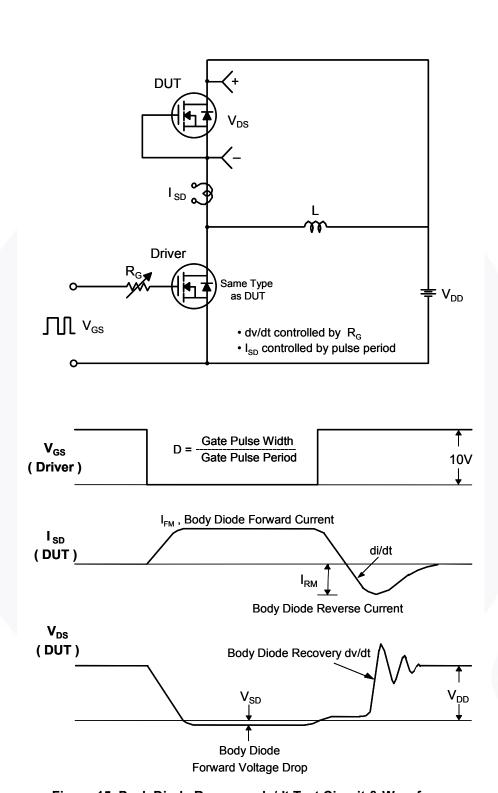
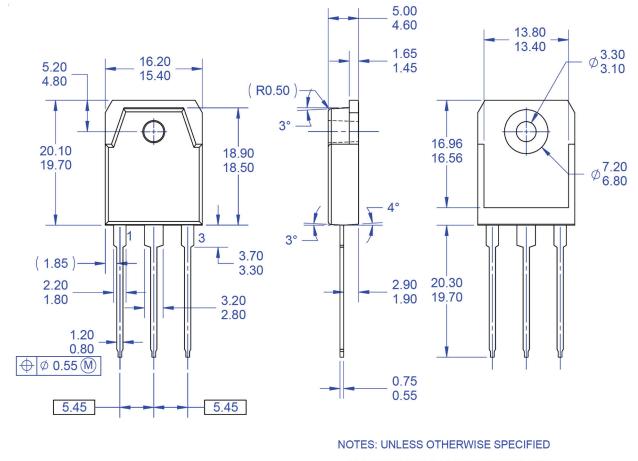
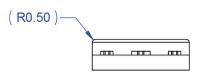


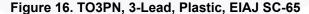
Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

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